

### General Description

The MY15N25NE5 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

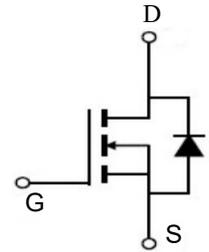
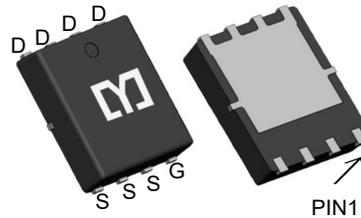


### Features

$X_{FU}$	250	X
$K$	18	C
$P_D(T_C=25^\circ C)$	58.7	W
$T_{FUTQP} \#cXI U? 10X+$	0.12	á

### Application

- Battery protection
- Load switch
- Uninterruptible power supply



### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY15N25NE5	PDFN5*6-8L	NULL	5000

### Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS} = 0V$ )	$V_{DS}$	250	V
Continuous Drain Current	$I_D$	18	A
Pulsed Drain Current	$I_{DM}$	36	A
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Single Pulse Avalanche Energy	$E_{AS}$	330	mJ
Avalanche Current	$I_{AR}$	3.2	A
Repetitive Avalanche Energy	$E_{AR}$	234	mJ
Power Dissipation ( $T_C = 25^\circ C$ )	$P_D$	58.7	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	$^\circ C$
Thermal Resistance, Junction-to-Case	$R_{thJC}$	2.13	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	52	

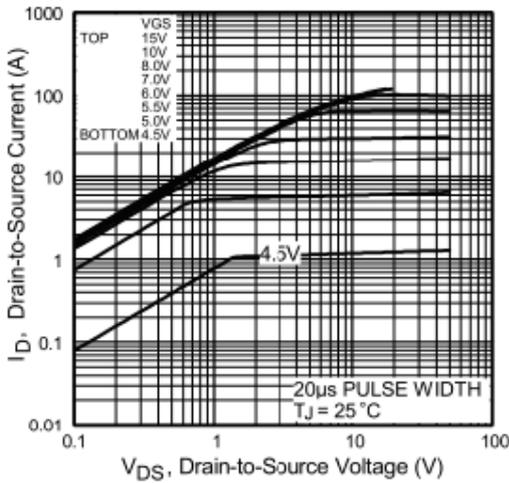
**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	250	--	--	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 250V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 25°C	--	--	1	μA
		V <sub>DS</sub> = 240V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C	--	--	100	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±25V	--	--	±100	nA
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.2	--	4.0	V
Drain-Source On-Resistance (Note3)	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.5A	--	0.12	0.16	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 25V, f = 1.0MHz	--	810	--	pF
Output Capacitance	C <sub>oss</sub>		--	110	--	
Reverse Transfer Capacitance	C <sub>rss</sub>		--	7	--	
Total Gate Charge	Q <sub>g</sub>	V <sub>DD</sub> = 240V, I <sub>D</sub> = 5.0A, V <sub>GS</sub> = 10V	--	8.4	--	nC
Gate-Source Charge	Q <sub>gs</sub>		--	1.2	--	
Gate-Drain Charge	Q <sub>gd</sub>		--	3.3	--	
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 150V, I <sub>D</sub> = 5.0A, R <sub>G</sub> = 25 Ω	--	20	--	ns
Turn-on Rise Time	t <sub>r</sub>		--	50	--	
Turn-off Delay Time	t <sub>d(off)</sub>		--	70	--	
Turn-off Fall Time	t <sub>f</sub>		--	53	--	
Continuous Body Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	--	--	5	A
Pulsed Diode Forward Current	I <sub>SM</sub>		--	--	20	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25°C, I <sub>SD</sub> = 5A, V <sub>GS</sub> = 0V	--	--	1.4	V
Reverse Recovery Time	t <sub>rr</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 5A, di <sub>F</sub> /dt = 100A/μs	--	263	--	ns
Reverse Recovery Charge	Q <sub>rr</sub>		--	1.9	--	μC

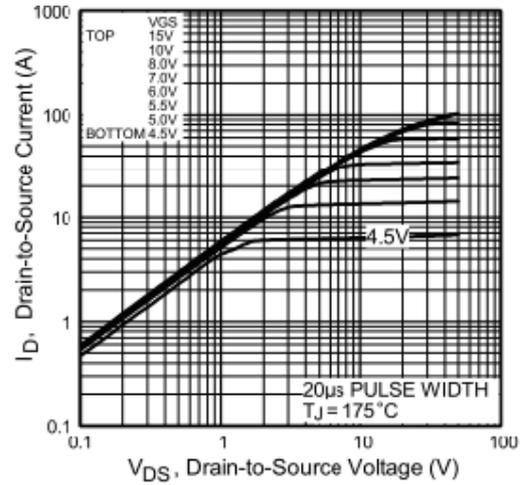
**Notes**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I<sub>AS</sub> = 3.2A, V<sub>DD</sub> = 50V, R<sub>G</sub> = 25 Ω, Starting T<sub>J</sub> = 25 °C
3. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

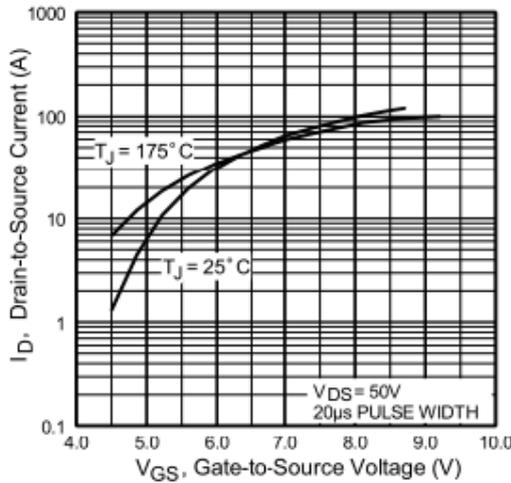
**Typical Characteristics**



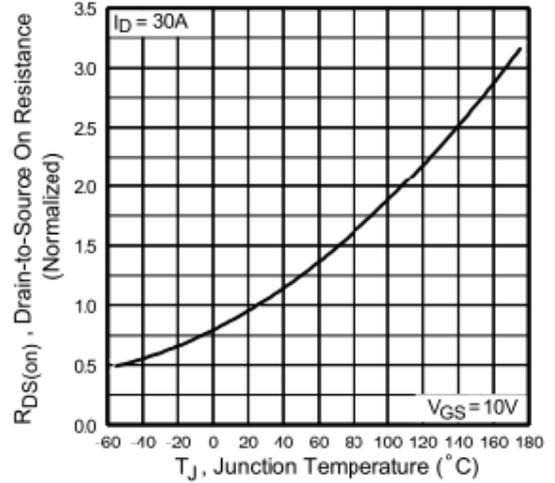
**Fig 1. Typical Output Characteristics**



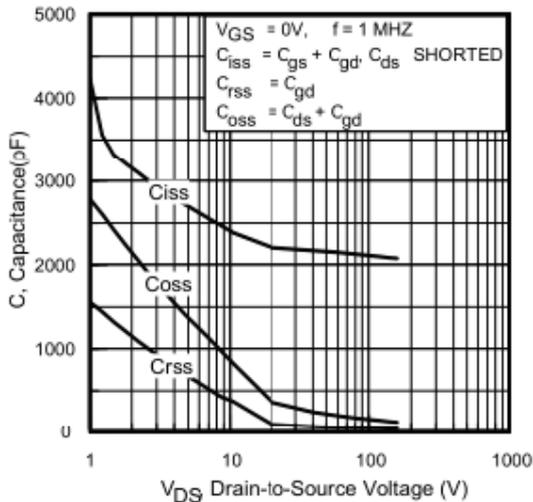
**Fig 2. Typical Output Characteristics**



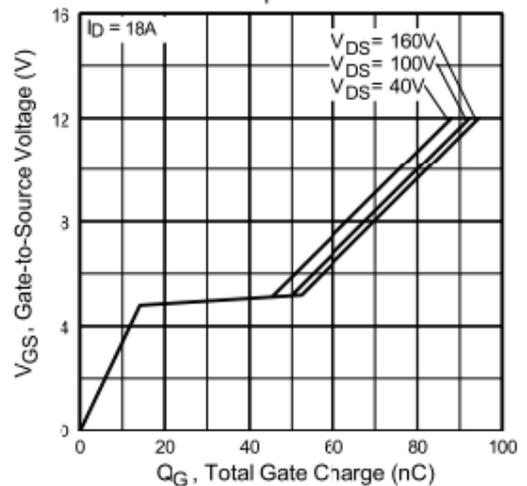
**Fig 3. Typical Transfer Characteristics**



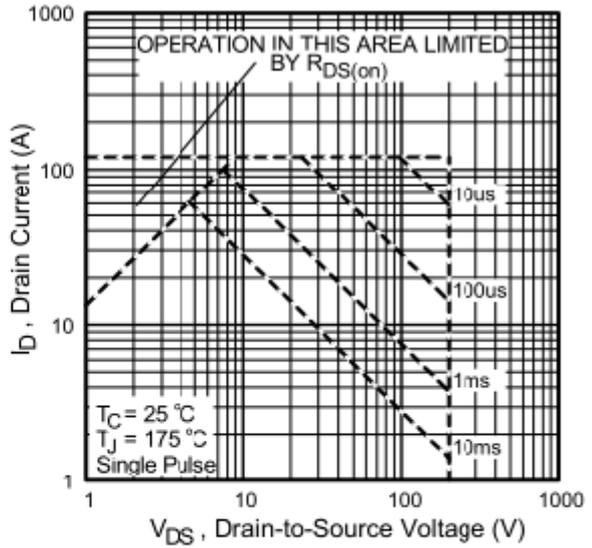
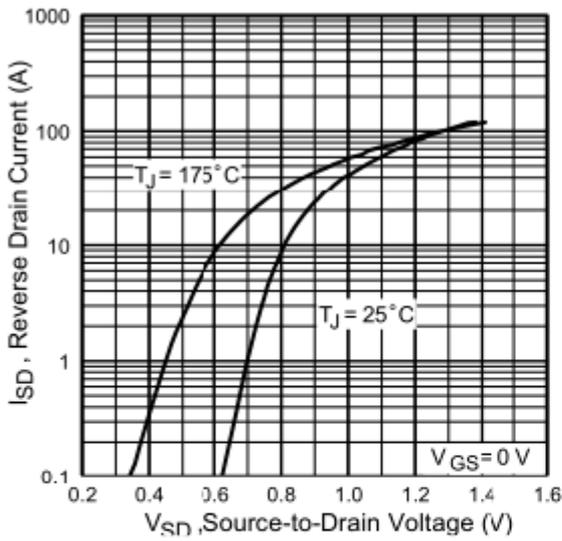
**Fig 4. Normalized On-Resistance Vs. Temperature**



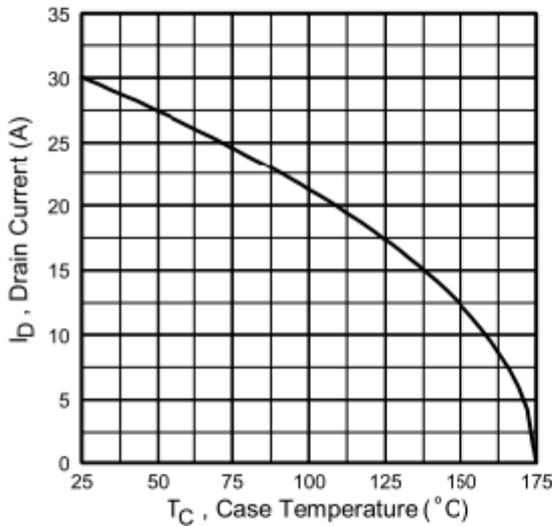
**Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage**



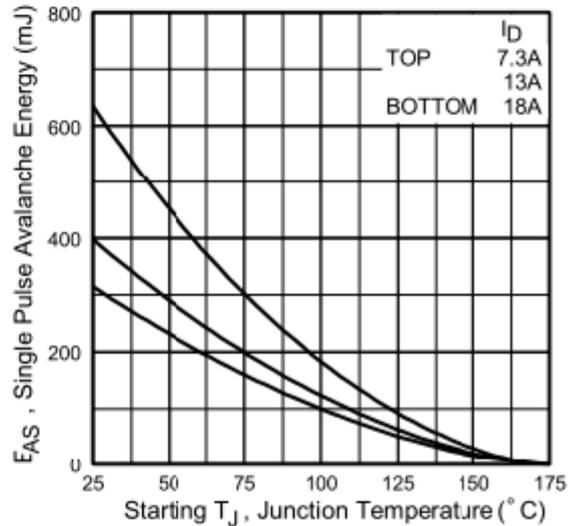
**Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage**



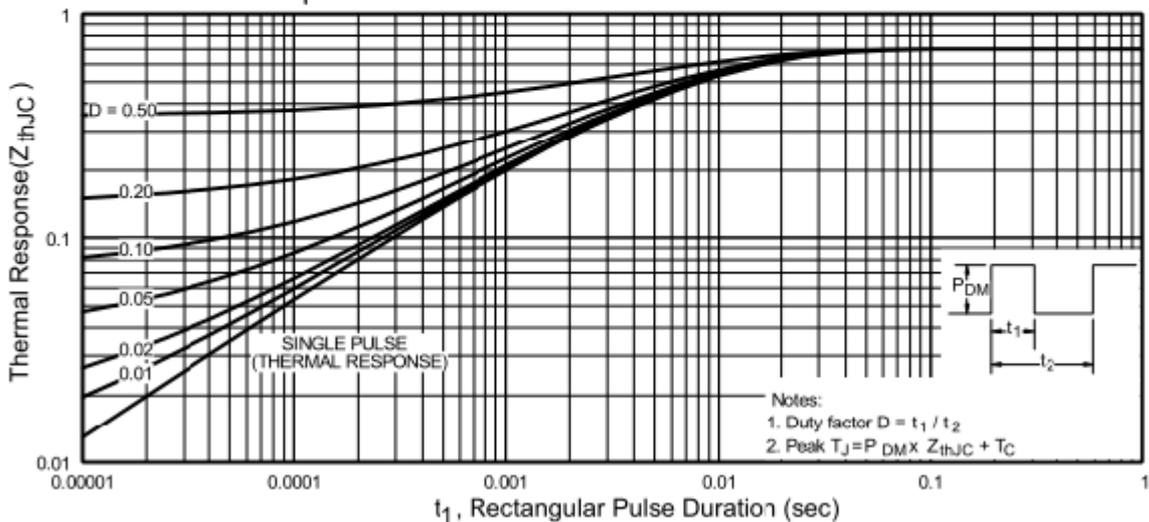
**Fig 8. Maximum Safe Operating Area**



**Fig 9. Maximum Drain Current Vs. Case Temperature**

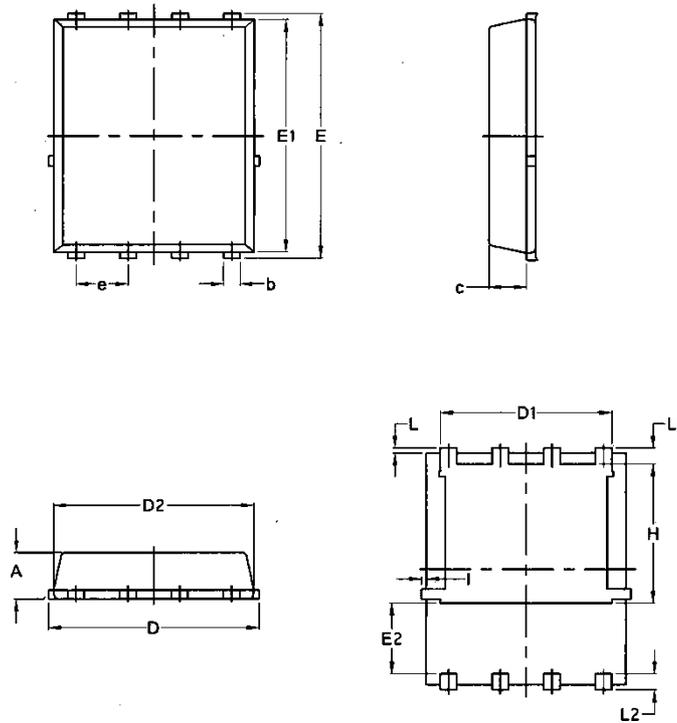


**Fig 12c. Maximum Avalanche Energy Vs. Drain Current**



**Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**Package Mechanical Data-DFN5\*6-8L-JQ Single**



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070